AMENDMENTS TO THE CLAIMS

1. (Previously Amended) A Method for fabricating a capacitor of a semiconductor device comprising:

depositing a nitride film and an oxide film over a substrate, the oxide film being deposited on the nitride film by chemical vapor deposition;

sequentially etching the oxide film and the nitride film using a patterned photoresist as a mask;

depositing a conductive layer over the substrate;

forming a photoresist pattern on the conductive layer;

etching the conductive layer using the photoresist pattern as a mask to form a lower electrode;

removing the photoresist using an etching gas that is non-reactive with respective to the lower electrode, wherein the etching gas is one of H_2O, a mixture of H_2 and O_2 in which an amount of H_2 is smaller than an amount of O_2, a mixture H_2O, NH_3, and N_2, a mixture of N_2 and NH_3, a mixture of NH_3 and H_2O, and a mixture of N_2 and H_2O; and

forming a dielectric film and an upper electrode on a surface of the lower electrode.

2. (Original) The method of claim 1, wherein the upper and lower electrodes are one of Ru, RuO_2 and a metal material alloyed with Ru.

3. (CANCELLED)

4. (Currently Amended) A method for fabricating a capacitor of a semiconductor device comprising:

~~depositing a nitride film and an oxide film over a semiconductor substrate, the oxide film being deposited on the nitride film by chemical vapor deposition;~~

~~sequentially etching the oxide film and the nitride film using a patterned photoresist as a mask;~~

forming a conductive region on a ~~the~~ semiconductor substrate;

forming an interleaving insulating film having a contact hole therein over the conductive region;

forming a contact plug within the contact hole;

forming insulating film patterns on the interleaving insulating film to expose the contact plug and the interleaving insulating film adjacent to the contact plug;

depositing a barrier film and a first conductive layer on the contact plug and the insulating film patterns;

forming a photoresist over the contact plug between the insulating film patterns;

sequentially removing the first conductive layer and the barrier film on the insulating film patterns using the photoresist as a mask, thereby forming a lower electrode and a barrier film in a U-shape in cross-section;

removing the photoresist using an etching gas that is non-reactive with respective to the lower electrode, wherein the etching gas is one of H_2O, a mixture of H_2 and O_2 in which an amount of H_2 is smaller than an amount of O_2, a mixture H_2O, NH_3, and N_2, a mixture of N_2 and NH_3, a mixture of NH_3 and H_2O, and a mixture of N_2 and H_2O;

removing the insulating film patterns; and

sequentially forming a dielectric film and an upper electrode on the lower electrode and the barrier film.

5. (Original) The method of claim 4, wherein the lower electrode is one of Ru, RuO_2 and a metal material alloyed with Ru.

6. (CANCELLED)

7. (Previously Amended) The method of claim 4, wherein the insulating film patterns comprise an oxide film.

8. (Previously Amended) The method of claim 4, wherein the insulating film patterns are formed by stacking two insulating films.

9. (Original) The method of claim 8, wherein the two insulating films are a nitride film and an oxide film.

10. (Original) The method of claim 4, wherein the barrier film is only formed on the contact plug within the contact hole.

11. (CANCELLED)

12. (CANCELLED)